
2SC4367

Silicon NPN Epitaxial

HITACHI

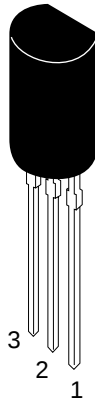
ADE-208-1105 (Z)
1st. Edition
Mar. 2001

Application

High Frequency amplifier

Outline

TO-92MOD



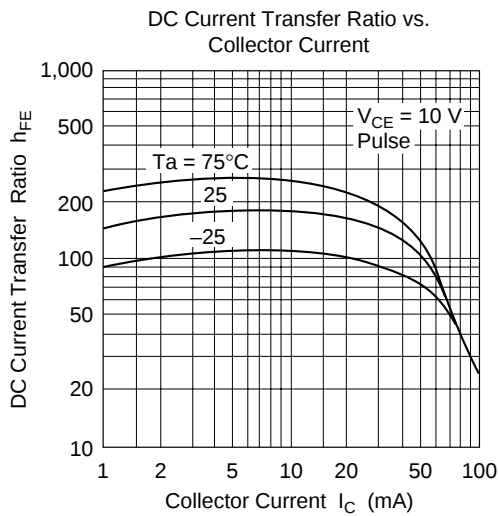
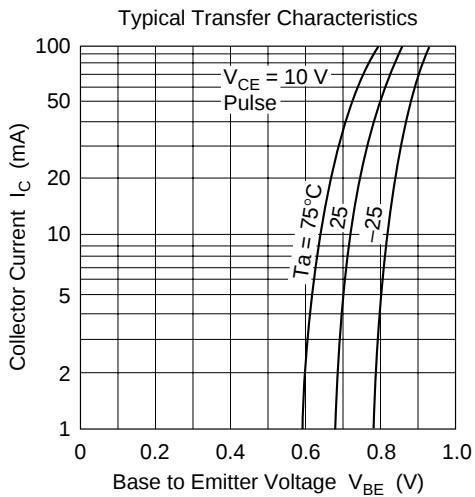
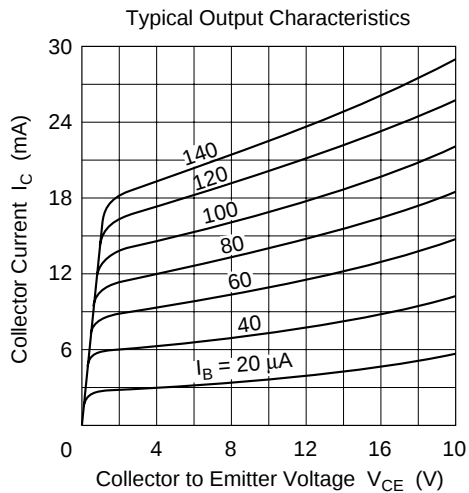
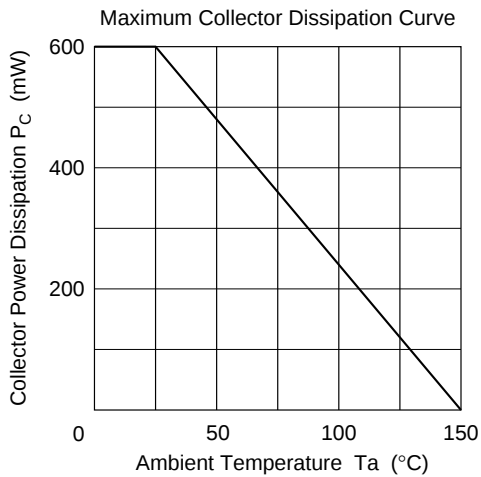
- 1. Emitter
- 2. Collector
- 3. Base

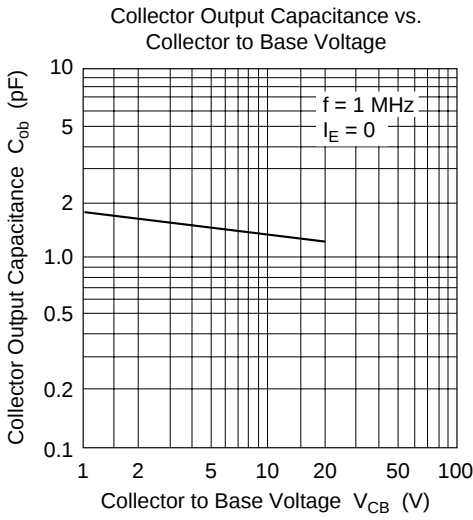
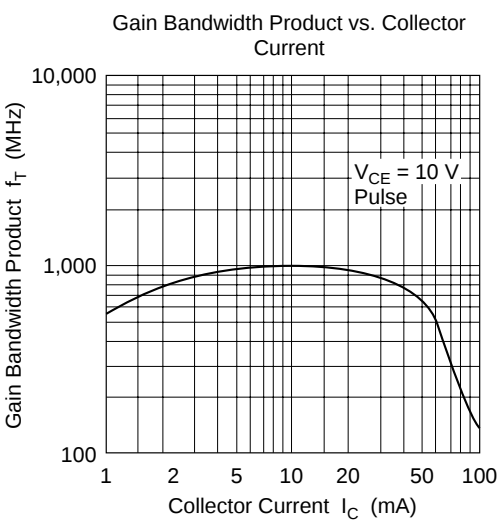
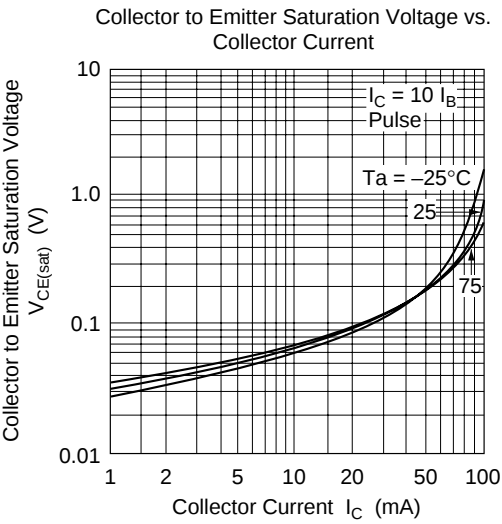
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_{C}	100	mA
Collector peak current	$i_{\text{C (peak)}}$	200	mA
Collector power dissipation	P_{C}	600	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

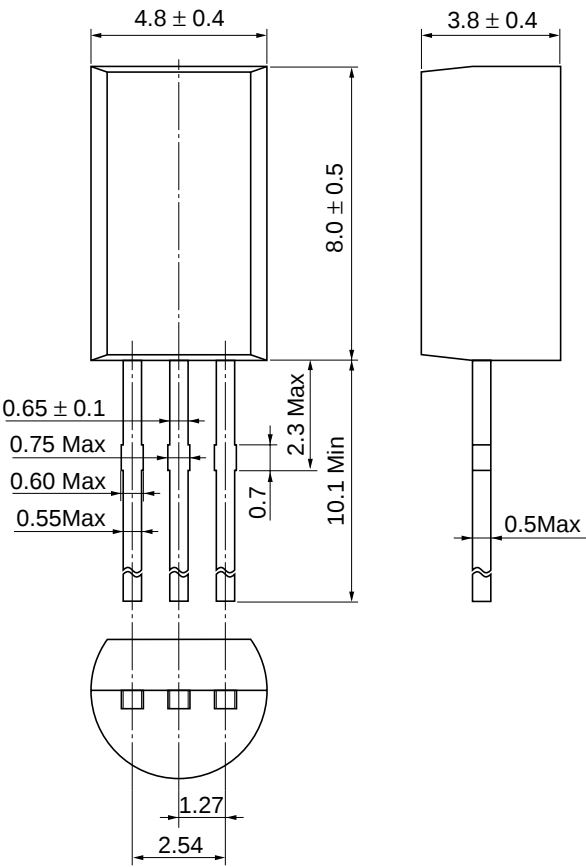
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	30	—	—	V	$I_{\text{C}} = 10\ \mu\text{A}$, $I_{\text{E}} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	20	—	—	V	$I_{\text{C}} = 3\ \text{mA}$, $R_{\text{BE}} = \infty$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	3	—	—	V	$I_{\text{E}} = 10\ \mu\text{A}$, $I_{\text{C}} = 0$
Collector cutoff current	I_{CBO}	—	—	1.0	μA	$V_{\text{CB}} = 10\ \text{V}$, $I_{\text{E}} = 0$
DC current transfer ratio	h_{FE}	40	—	—		$V_{\text{CE}} = 10\ \text{V}$, $I_{\text{C}} = 10\ \text{mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	1.0	V	$I_{\text{C}} = 20\ \text{mA}$, $I_{\text{B}} = 4\ \text{mA}$
Gain bandwidth product	f_{T}	600	1000	—	MHz	$V_{\text{CE}} = 10\ \text{V}$, $I_{\text{C}} = 10\ \text{mA}$
Collector output capacitance	C_{ob}	—	1.3	—	pF	$V_{\text{CB}} = 10\ \text{V}$, $I_{\text{E}} = 0$, $f = 1\ \text{MHz}$





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.35 g

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